



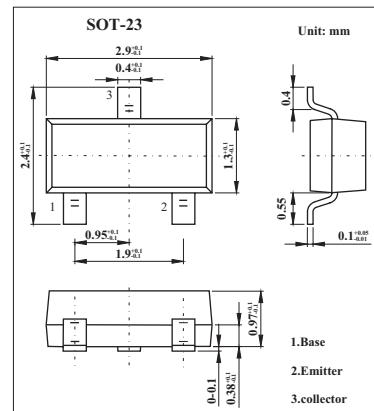
DONGGUAN NANJING ELECTRONICS LTD.,

NPN Silicon Transistor

2SC1623

■ Features

- High DC Current Gain:
 $hFE = 200$ TYP.
 $V_{CE} = 6.0$ V, $I_C = 1.0$ mA
- High Voltage:
 $V_{CEO} = 50$ V

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	60	V
Collector to emitter voltage	V_{CEO}	50	V
Emitter to base voltage	V_{EBO}	5	V
Collector current (DC)	I_C	100	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 60$ V, $I_E = 0$			0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 5$ V, $I_C = 0$			0.1	μA
DC current gain *	hFE	$V_{CE} = 6$ V, $I_C = 1$ mA	90	200	600	
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_C = 100$ mA, $I_B = 10$ mA		0.15	0.3	V
Base-emitter saturation voltage *	$V_{BE(sat)}$	$I_C = 100$ mA, $I_B = 10$ mA		0.86	1	V
Base-emitter voltage *	V_{BE}	$V_{CE} = 6$ V, $I_C = 1$ mA	0.55	0.62	0.65	V
Output capacitance	C_{ob}	$V_{CB} = 6$ V, $I_E = 0$, $f = 1.0$ MHz		3.0		pF
Transiton Frequency	f_T	$V_{CE} = 6$ V, $I_E = -10$ mA		250		MHz

*. PW≤350μs,duty cycle≤2%

■ hFE Classification

Marking	L4	L5	L6	L7
hFE	90 to 180	135 to 270	200 to 400	300 to 600

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■ Typical Characteristics

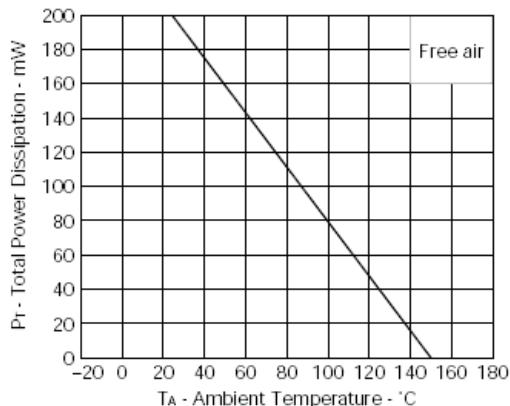


Fig.1 Total power dissipation vs. ambient temperature

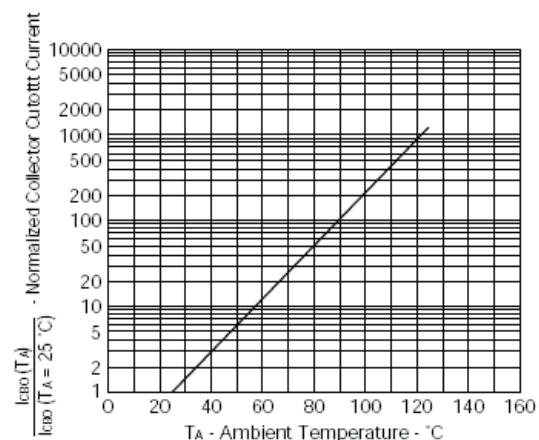


Fig.2 Normalized collector cutoff current vs. ambient temperature

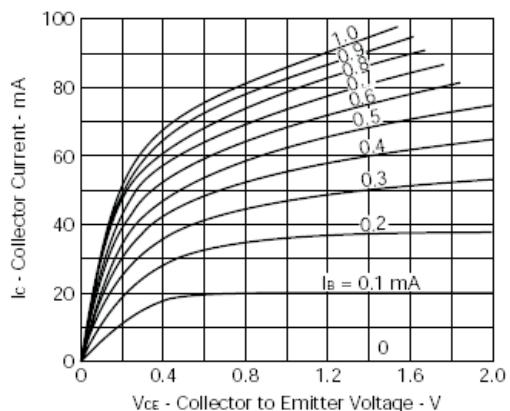


Fig.3 Collector current vs. collector to emitter voltage

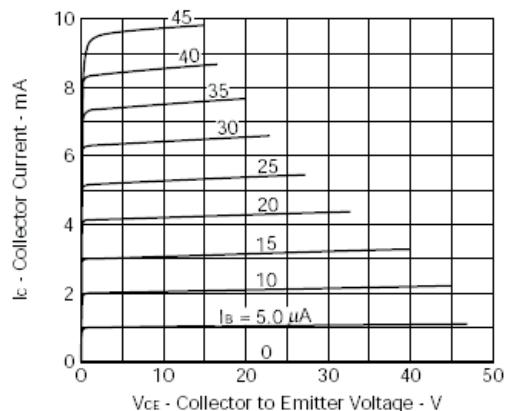


Fig.4 Collector current vs. collector to emitter voltage

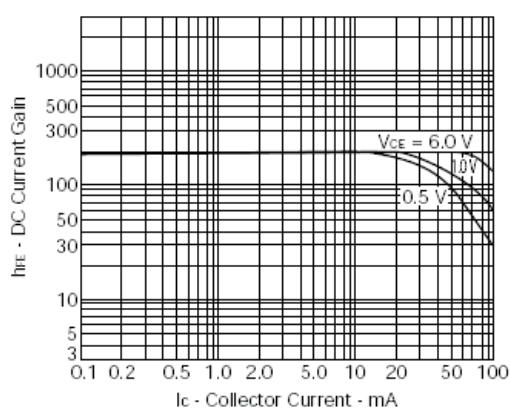


Fig.5 DC current gain vs. collector current

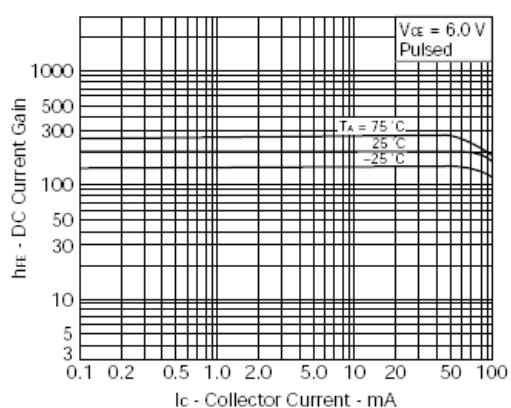


Fig.6 DC current gain vs. Collector current

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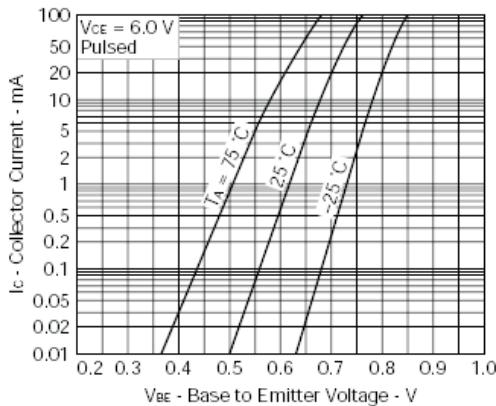


Fig. 7 Collector current vs. base to emitter voltage

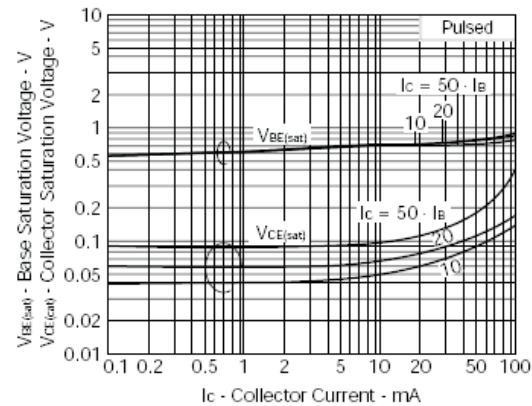


Fig. 8 Collector and base saturation voltage vs. collector current

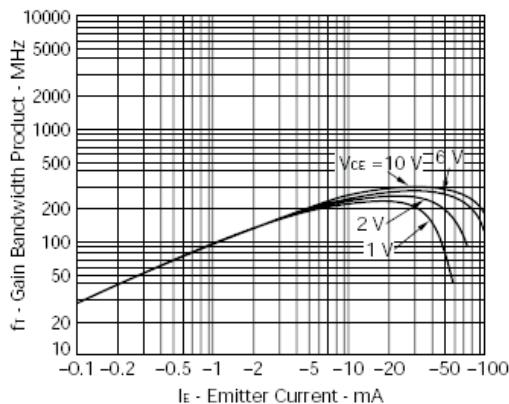


Fig. 9 Gain bandwidth product vs. emitter current

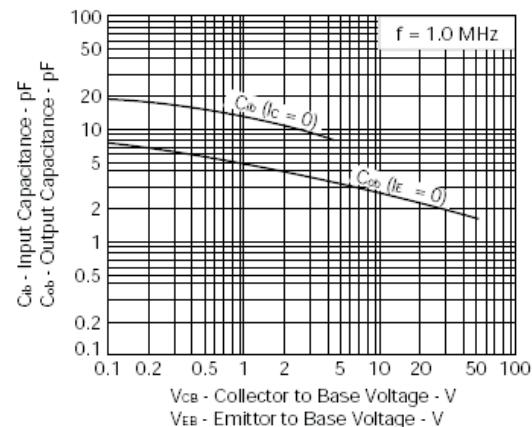


Fig. 10 Input and output capacitance vs. reverse voltage

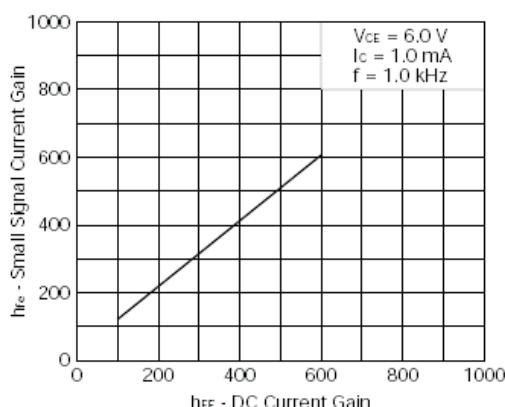


Fig. 11 Small signal current gain vs. DC current gain

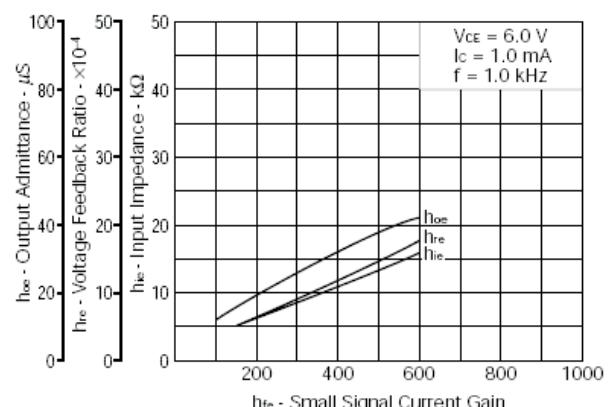


Fig. 12 Input impedance voltage feedback ratio and output admittance vs. small signal current gain

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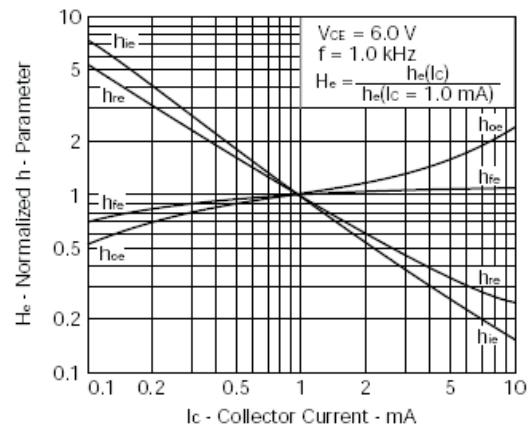


Fig.13 Normalized h-parameter vs.collector current

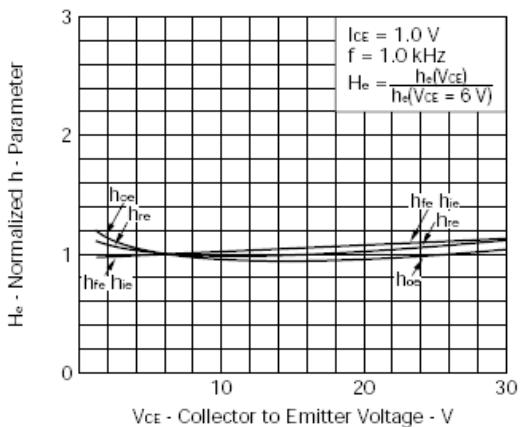


Fig.14 Normalized h-parameter vs.collector to emitter voltage